



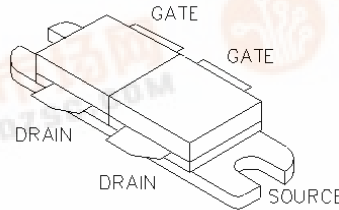
polyfet rf devices

SR341

General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features low feedback and output capacitances resulting in high F_t transistors with high input impedance and high efficiency.



SILICON GATE ENHANCEMENT MODE

RF POWER VDMOS TRANSISTOR

300.0 Watts Push - Pull

Package Style AR

HIGH EFFICIENCY, LINEAR

HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (T = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
500 Watts	0.30 °C/W	200 °C	-65 °C to 150 °C	25.0 A	125V	125V	20 V

RF CHARACTERISTICS (300.0 WATTS OUTPUT)

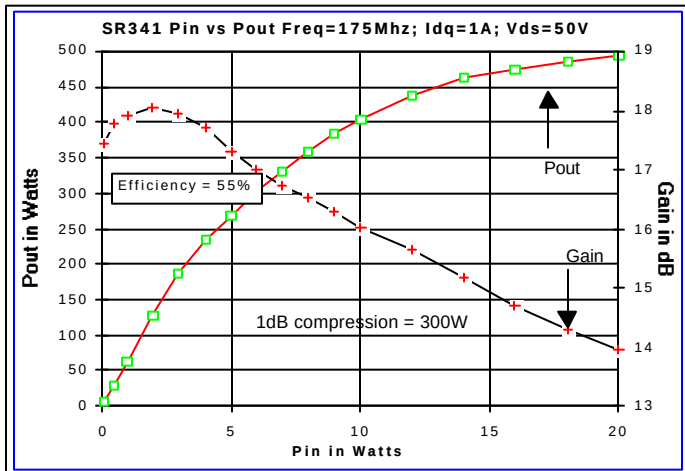
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	16			dB	Idq = 0.80 A, Vds = 50.0 V, F = 175MHz
η	Drain Efficiency		65		%	Idq = 0.80 A, Vds = 50.0 V, F = 175MHz
VSWR	Load Mismatch Tolerance			20:1	Relative	Idq = 0.80 A, Vds = 50.0 V, F = 175MHz

ELECTRICAL CHARACTERISTICS (EACH SIDE)

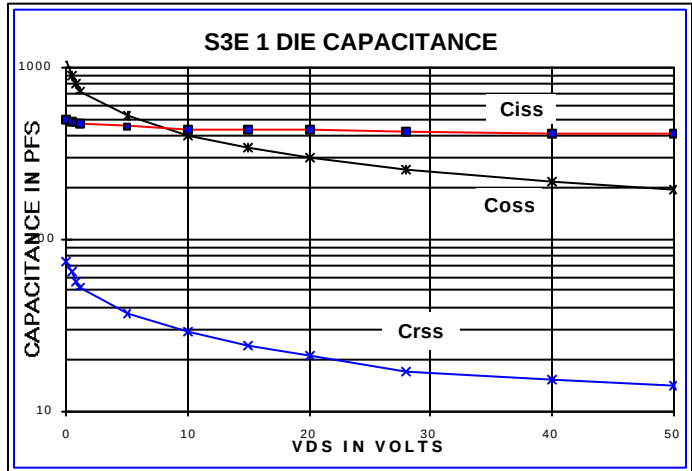
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	125			V	Ids = 40.00 mA, Vgs = 0V
Idss	Zero Bias Drain Current			5.0	mA	Vds = 50.0 V, Vgs = 0V
Igss	Gate Leakage Current			1	uA	Vds = 0V Vgs = 30V
Vgs	Gate Bias for Drain Current	1		7	V	Ids = 0.30 A, Vgs = Vds
gM	Forward Transconductance		5.5		Mho	Vds = 10V, Vgs = 5V
Rdson	Saturation Resistance		0.30		Ohm	Vgs = 20V, Ids = 6.00 A
Idsat	Saturation Current		35.00		Amp	Vgs = 20V, Vds = 10V
Ciss	Common Source Input Capacitance		400.0		pF	Vds = 50.0 Vgs = 0V, F = 1 MHz
Crss	Common Source Feedback Capacitance		15.0		pF	Vds = 50.0 Vgs = 0V, F = 1 MHz
Coss	Common Source Output Capacitance		200.0		pF	Vds = 50.0 Vgs = 0V, F = 1 MHz

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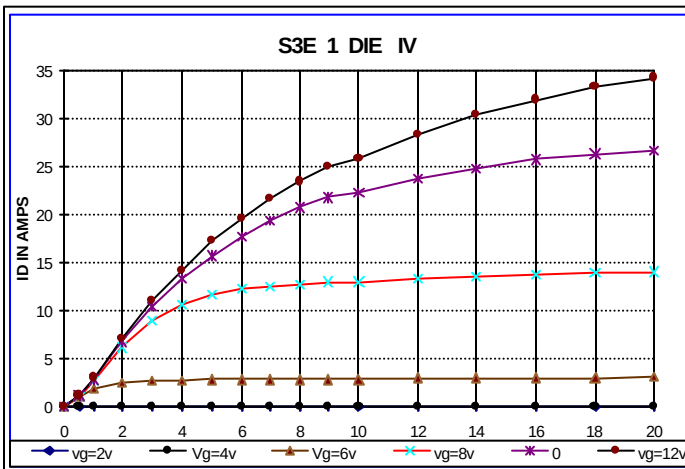
POUT VS PIN GRAPH



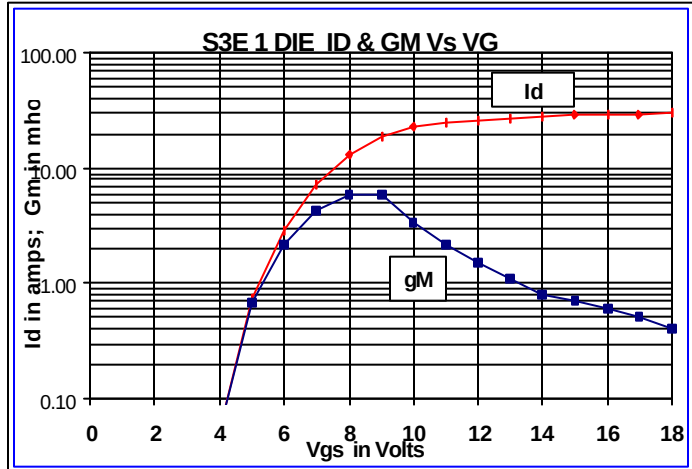
CAPACITANCE VS VOLTAGE



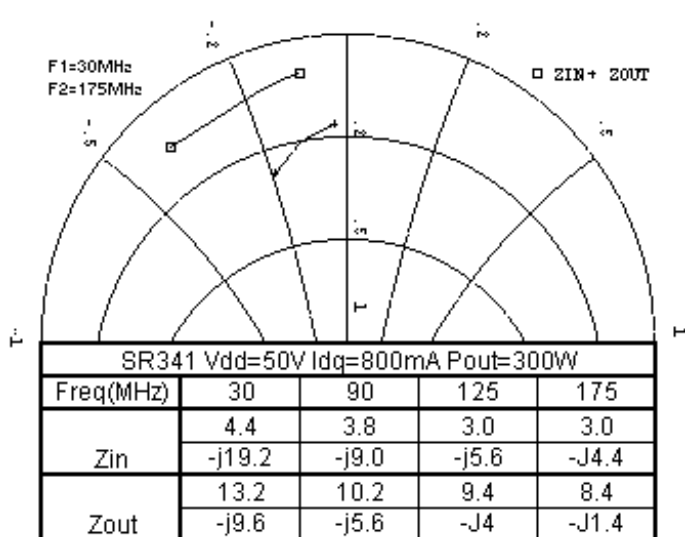
IV CURVE



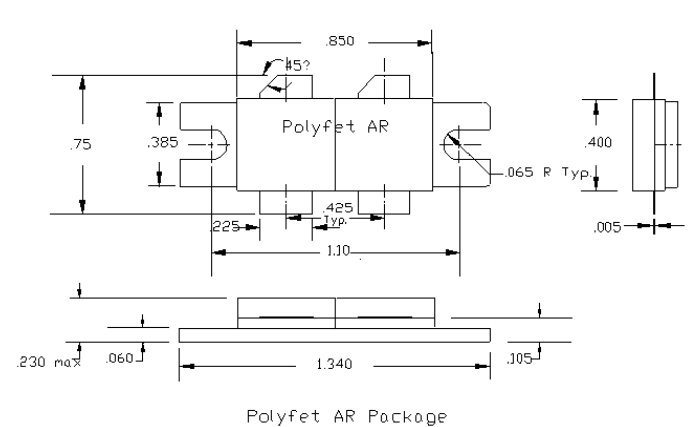
ID & GM VS VGS



Zin Zout



PACKAGE DIMENSIONS IN INCHES



Tolerance .XX +/-0.01 .XXX +/- .005 inches